

2SB1554

Silicon PNP epitaxial planar type

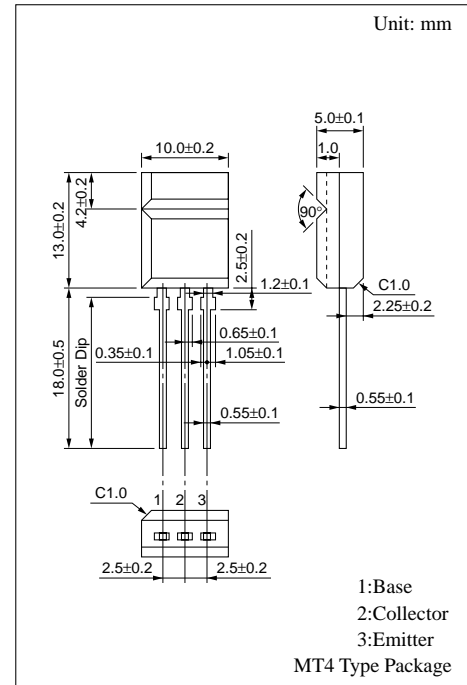
For power amplification

■ Features

- High forward current transfer ratio h_{FE} which has satisfactory linearity
- Allowing automatic insertion with radial taping

■ Absolute Maximum Ratings ($T_C=25^\circ\text{C}$)

Parameter	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	-60	V
Collector to emitter voltage	V_{CEO}	-60	V
Emitter to base voltage	V_{EBO}	-20	V
Peak collector current	I_{CP}	-8	A
Collector current	I_C	-4	A
Base current	I_B	-2	A
Collector power dissipation	P_C	$T_C=25^\circ\text{C}$	15
		$T_a=25^\circ\text{C}$	2
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$



■ Electrical Characteristics ($T_C=25^\circ\text{C}$)

Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	I_{CBO}	$V_{CB} = -60\text{V}, I_E = 0$			-10	μA
	I_{CEO}	$V_{CE} = -50\text{V}, I_B = 0$			-50	μA
Emitter cutoff current	I_{EBO}	$V_{EB} = -15\text{V}, I_C = 0$			-10	μA
Collector to emitter voltage	V_{CEO}	$I_C = -10\text{mA}, I_B = 0$	-60			V
Forward current transfer ratio	h_{FE1}^*	$V_{CE} = -4\text{V}, I_C = -0.8\text{A}$	80		400	
	h_{FE2}	$V_{CE} = -4\text{V}, I_C = -2\text{A}$	30			
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = -2\text{A}, I_B = -100\text{mA}$			-1.0	V
Base to emitter saturation voltage	$V_{BE(sat)}$	$I_C = -2\text{A}, I_B = -100\text{mA}$			-1.5	V
Transition frequency	f_T	$V_{CE} = -10\text{V}, I_C = -0.5\text{A}, f = 1\text{MHz}$		25		MHz
Turn-on time	t_{on}	$I_C = -2\text{A}, I_{B1} = -100\text{mA}, I_{B2} = 100\text{mA}, V_{CC} = -50\text{V}$		0.4		μs
Storage time	t_{stg}			0.6		μs
Fall time	t_f				0.25	μs

* h_{FE1} Rank classification

Rank	Q	P	O
h_{FE1}	80 to 160	120 to 240	200 to 400

